

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(polysilicon with substrate with (ldd or (lightly adj doped adj drain))) and ((gate adj (insulating or dielectric or insulation))) and (gate adj buffer) and drain and source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:14
L2	192	(low adj temperature adj polysilicon adj thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:15
L3	24	(low adj temperature adj polysilicon adj thin adj film adj transistor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:16
L4	8	(low adj temperature adj polysilicon adj thin adj film adj transistor).clm. and (ldd or (lightly adj doped))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:16
L5	6	(low adj temperature adj polysilicon adj thin adj film adj transistor).clm. and (ldd or (lightly adj doped)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:17
L6	4	(low adj temperature adj polysilicon adj thin adj film adj transistor).clm. and (ldd or (lightly adj doped)).clm. and buffer.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:20
L7	10	((low adj temperature adj polysilicon adj thin adj film adj transistor) or ltps) and (ldd or (lightly adj doped)).clm. and buffer.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:25
L8	4	((low adj temperature adj polysilicon adj thin adj film adj transistor) or ltps) and (substrate same polysilicon same (ldd or (lightly adj doped)) same (gate adj (insulating or insulation or dielectric)) same buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:26

L20	382	((buffer adj layer) near10 (gate adj (insulation or insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:52
L21	6	((gate adj buffer adj layer) near10 (gate adj (insulation or insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:53
L22	382	((buffer adj layer) near10 (gate adj (insulation or insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:54
L23	63	((buffer adj layer) near10 (over or above or top or on) near10 (gate adj (insulation or insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:54
L24	33	((buffer adj layer) near5 (over or above or top or on) near5 (gate adj (insulation or insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:55
L25	17	((buffer adj layer) near5 (over or above or top or on) near5 (gate adj (insulation or insulating or dielectric))) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 17:55